Docket No.: GR99P3457

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant

HARALD KUHN ET AL.

Filed

CONCURRENTLY HEREWITH

Title

DEVICE HAVING A FOIL-LINED CRUCIBLE FOR THE

SUBLIMATION GROWTH OF AN SIC SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks, Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent 5,667,587 (Glass et al.), dated September 16, 1997;

U.S. Patent 4,186,046 (DeLai et al.), dated January 29, 1980;

U.S. Patent 5,895,526 (Kitoh et al.), dated April 20, 1999;

German Patent Application DE 32 30 727 C2 (Ziegler), dated February 23, 1984, method to produce single crystals from silicon carbide SIC;

German published Non-Prosecuted Patent Application DE 36 44 746 A1, dated July 14, 1988, method and device to grow crystals;

PCT WO 94/23096 (Völkl et al.), dated October 13, 1994;

PCT WO 97/27350 (Vodakov et al.), dated July 31, 1997;

Patent Abstracts of Japan 10 291 899 A (Naoki et al.), dated November 4, 1998;



Patent Abstracts of Japan 11 116 399 (Yasuo), dated April 27, 1999;

Patent Abstracts of Japan 11 116 398 (Shigehiro), dated April 27, 1999;

Hofmann, D. et al.: "Use of Ta Container Material for Quality Improvement of SiC crystals grown by the Sublimation Technique", IOP Publishing Ltd, 1996, pp. 29-32;

Mokhov, E. et al.: "Growth of Silicon Carbide Bulk Crystals by the Sublimation Sandwich Method", Elsevier Science S.A., 1997, pp. 317-323;

"Tantal, Tantal-Legierung" (tantalum, tantalum alloy), Römpp Chemie-Lexikon (chemistry encyclopedia), Vol. 9, 1995, pp. 4453-4455;

International Search Report, dated July 7, 1999;

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,

For Applicants

WERNER H. STEMER FEG. NO. 34-956

Date: January 7, 2002

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SHEET 2 OF 2



FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))

Attorney Docket No.: GR99P3457	
Appl. No.	

Applicant HARALD KUHN ET AL.

Filing Date January 7, 2002 Group Art Unit

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EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
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FOREIGN PATENT DOCUMENT

					SUB	TRANSL.
	DOCUMENT NO.	DATE	COUNTRY	CLASS	CLASS	YES NO
J	11 116 399	4/27/99	Japan			
K	11 116 398	4/27/99	Japan			
L						
М						
N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	"Tantal, Tantal-Legierung" (tantalum, tantalum alloy), Römpp Chemie-Lexikon (chemistry encyclopedia), Vol. 9, 1995, pp. 4453-4455;

EXAMINER

DATE CONSIDERED

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SHEET 1 OF 2



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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))

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INITIALS	Ļ	PATENT NO.	DATE	PATENTEE	CLASS	CLASS	DATE
	Α	5,667,587	9/16/97	Glass et al.			
	В	4,186,046	1/29/80	DeLai et al.			
	С	5,895,526	4/20/99	Kitoh et al.			
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FOREIGN PATENT DOCUMENT

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
 J	32 30 727 C2	2/23/84	Germany			
 К	36 44 746 a1	7/14/88	Germany			
L	WO 94/23096	10/13/94	WIPO			
М	WO 97/27350	7/31/97	WIPO			
N	10 291 899 A	11/4/98	Japan			

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